

## SWITCHING REGULATOR APPLICATIONS

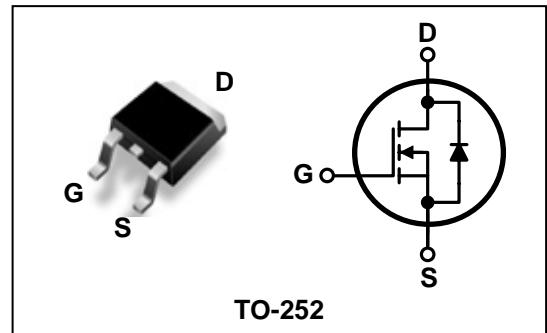
### Features

- High Voltage:  $BV_{DSS}=600V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=9.8pF$ (Typ.)
- Low gate charge :  $Q_g=12nC$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=2.5\Omega$ (Max.)

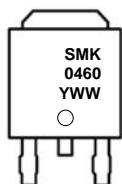
### Ordering Information

Type No.	Marking	Package Code
SMK0460D	SMK0460	TO-252

### PIN Connection



### Marking Diagram



Column 1 2 : Device Code  
 Column 3: Production Information  
 e.g.) YWW  
 - . Y: Year Code  
 - . WW: Week Code

### Absolute maximum ratings ( $T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit				
Drain-source voltage	$V_{DSS}$	600	V				
Gate-source voltage	$V_{GSS}$	$\pm 30$	V				
Drain current (DC)	$I_D$	<table border="1"> <tr> <td>(<math>T_c=25^\circ C</math>)</td> <td>4</td> </tr> <tr> <td>(<math>T_c=100^\circ C</math>)</td> <td>2.53</td> </tr> </table>	( $T_c=25^\circ C$ )	4	( $T_c=100^\circ C$ )	2.53	A
( $T_c=25^\circ C$ )	4						
( $T_c=100^\circ C$ )	2.53						
Drain current (Pulsed) *	$I_{DM}$	16	A				
Drain Power dissipation	$P_D$	48	W				
Avalanche current (Single)	$I_{AS}$	4	A				
Single pulsed avalanche energy	$E_{AS}$	225	mJ				
Avalanche current (Repetitive)	$I_{AR}$	4	A				
Repetitive avalanche energy	$E_{AR}$	10	mJ				
Junction temperature	$T_J$	150	$^\circ C$				
Storage temperature range	$T_{stg}$	-55~150					

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max	Unit
Thermal resistance	$R_{th(J-C)}$	-	2.6	$^\circ C/W$
	$R_{th(J-a)}$	-	62.5	

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$I_D=250\mu\text{A}, V_{GS}=0$	600	-	-	V
Gate-threshold voltage	$V_{GS(\text{th})}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source leakage current	$I_{\text{DSS}}$	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-source leakage	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-Source on-resistance <sup>(4)</sup>	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=2.0\text{A}$	-	2.1	2.5	$\Omega$
Forward transfer admittance <sup>(4)</sup>	$g_{fs}$	$V_{DS}=10\text{V}, I_D=2.0\text{A}$	-	4.0	-	S
Input capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$	-	670	848	pF
Output capacitance	$C_{oss}$		-	57	71	
Reverse transfer capacitance	$C_{rss}$		-	9.8	12.2	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD}=300\text{V}, I_D=4\text{A}$ $R_G=25\Omega$	-	10	-	ns
Rise time	$t_r$		-	42	-	
Turn-off delay time	$t_{d(\text{off})}$		-	38	-	
Fall time	$t_f$		-	46	-	
Total gate charge	$Q_g$	$V_{DS}=480\text{V}, V_{GS}=10\text{V}$ $I_D=4\text{A}$	-	12	15	
Gate-source charge	$Q_{gs}$		-	4	-	nC
Gate-drain charge	$Q_{gd}$		-	3	-	

**Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

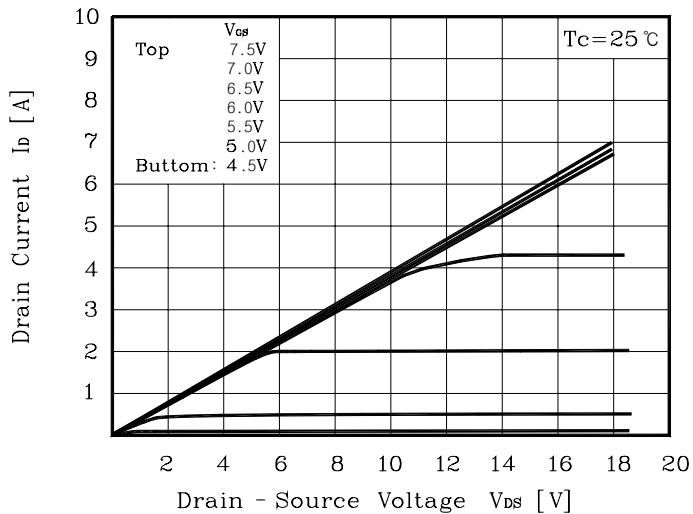
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Continuous source current	$I_s$	Integral reverse diode in the MOSFET	-	-	4	A
Source current (Pulsed) <sup>(1)</sup>	$I_{SM}$		-	-	16	
Forward voltage <sup>(4)</sup>	$V_{SD}$	$V_{GS}=0\text{V}, I_s=4\text{A}$	-	-	1.4	V
Reverse recovery time	$t_{rr}$	$I_s=4\text{A}$ $dI_s/dt=100\text{A}/\mu\text{s}$	-	300	-	ns
Reverse recovery charge	$Q_{rr}$		-	2.2	-	uC

Note :

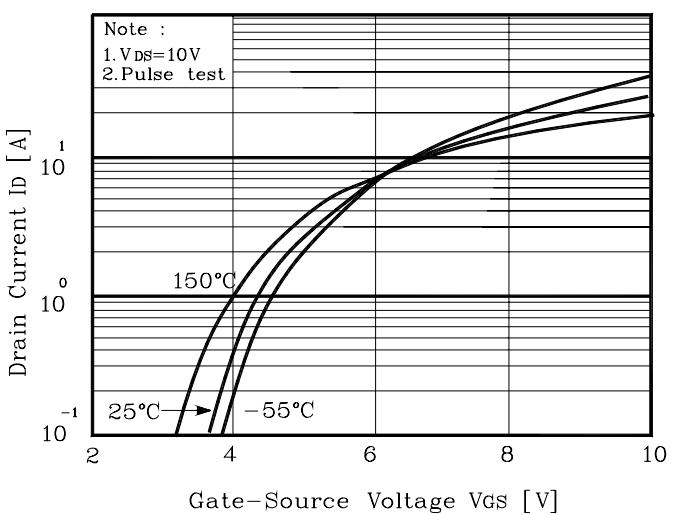
- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=25.9\text{mH}, I_{AS}=4\text{A}, V_{DD}=50\text{V}, R_G=27\Omega$ , Starting  $T_J = 25^\circ\text{C}$
- ③ Pulse Test : Pulse Width < 300us, Duty cycle  $\leq 2\%$
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

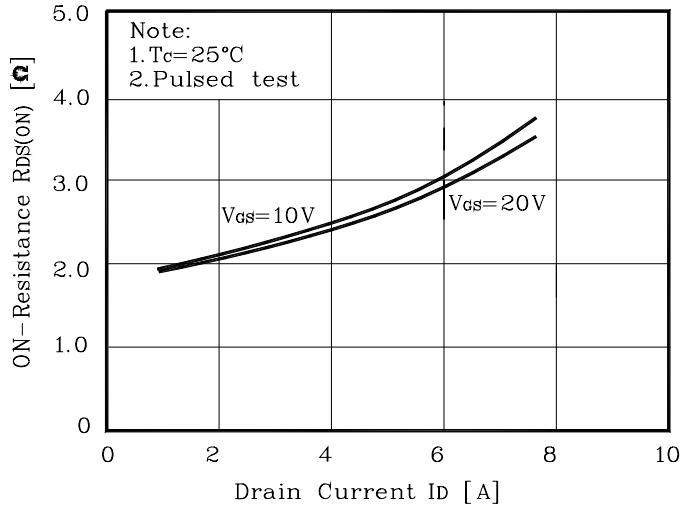
**Fig. 1  $I_D$  -  $V_{DS}$**



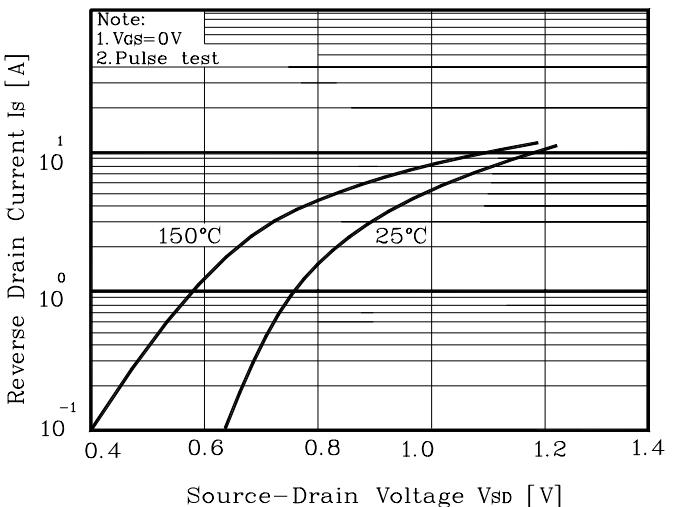
**Fig. 2  $I_D$  -  $V_{GS}$**



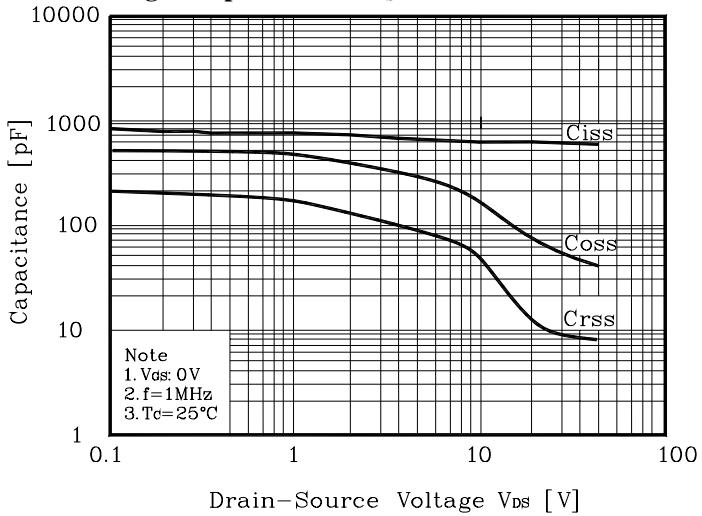
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



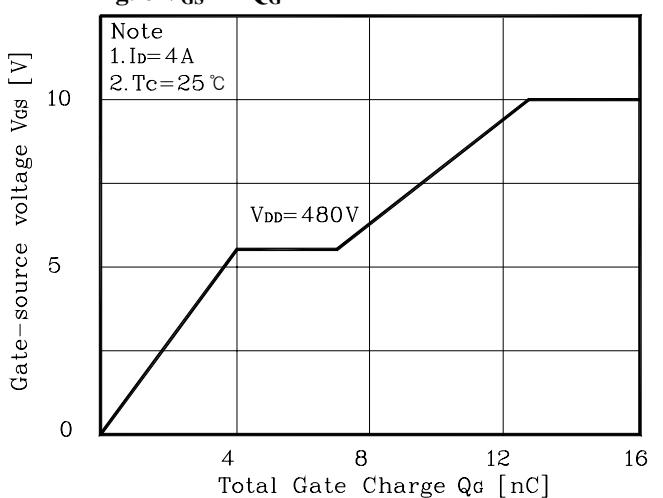
**Fig. 4  $I_S$  -  $V_{SD}$**



**Fig. 5 Capacitance -  $V_{DS}$**

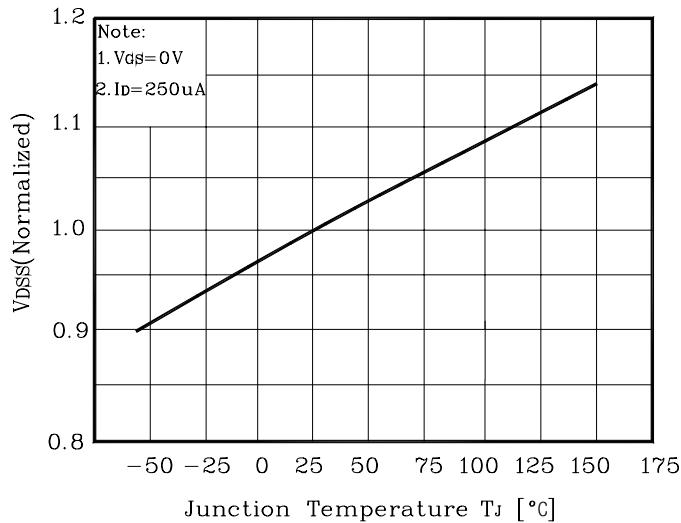


**Fig. 6  $V_{GS}$  -  $Q_G$**

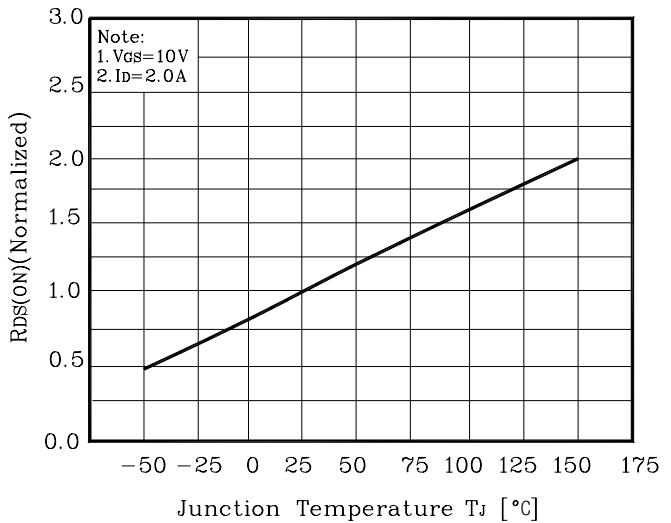


## Electrical Characteristic Curves

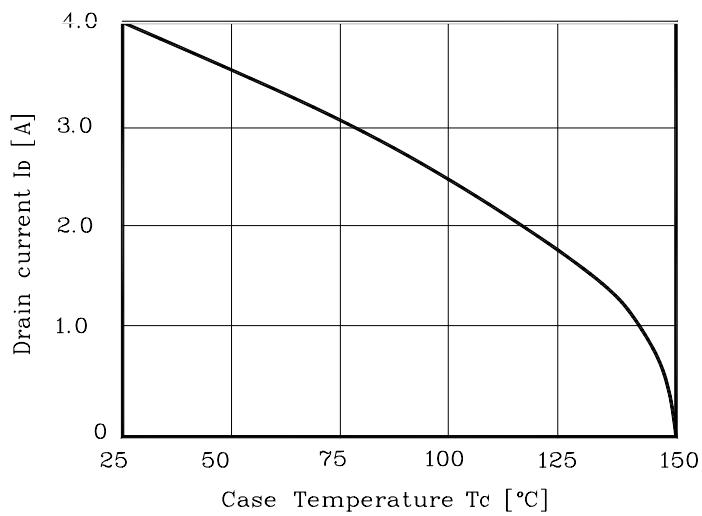
**Fig. 7  $V_{DSS}$  -  $T_J$**



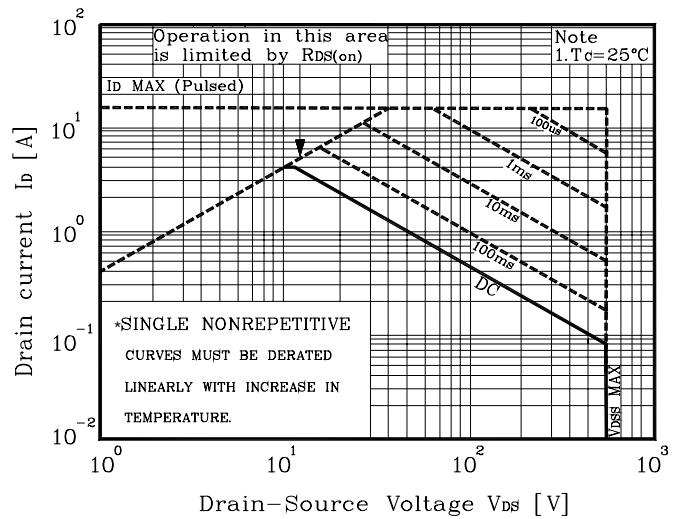
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



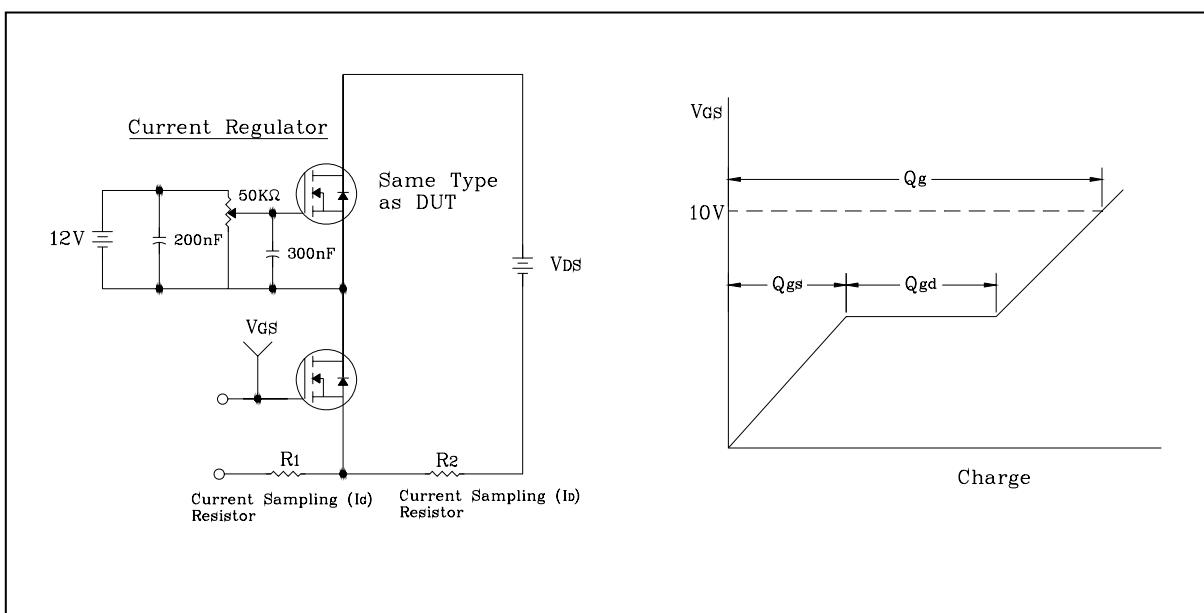
**Fig. 9  $I_D$  -  $T_C$**



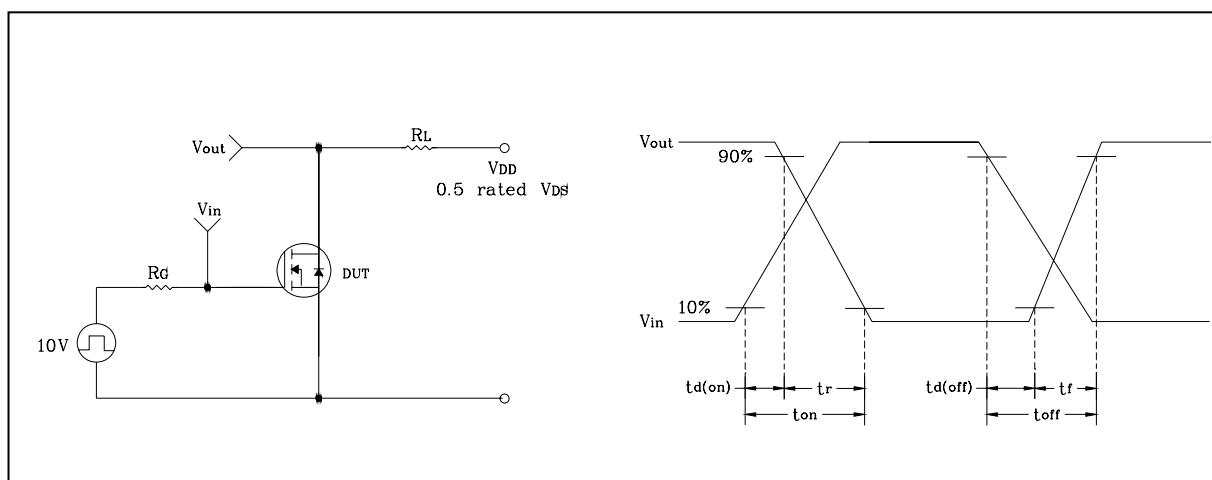
**Fig. 10 Safe Operating Area**



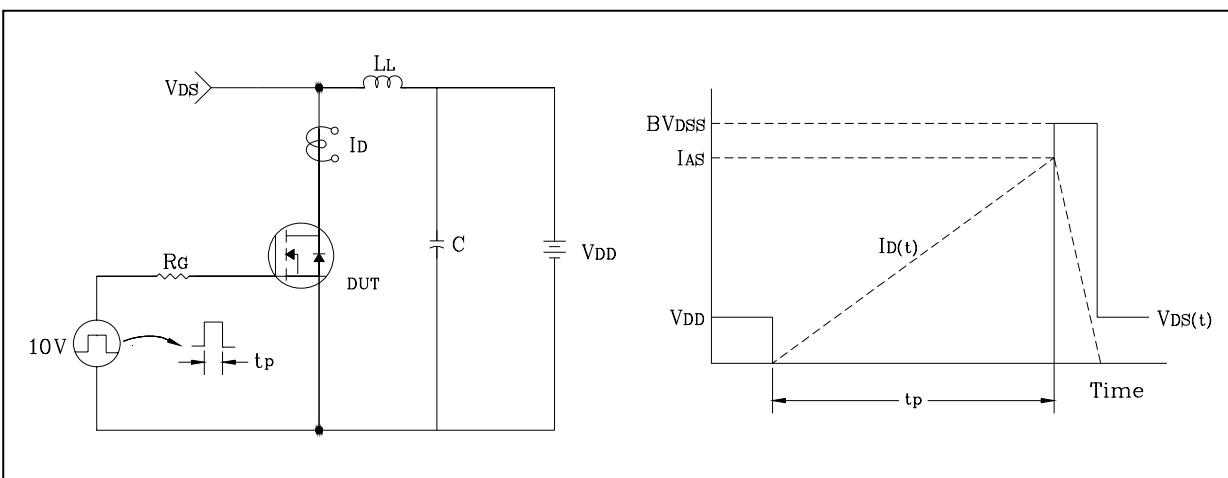
**Fig. 11 Gate Charge Test Circuit & Waveform**



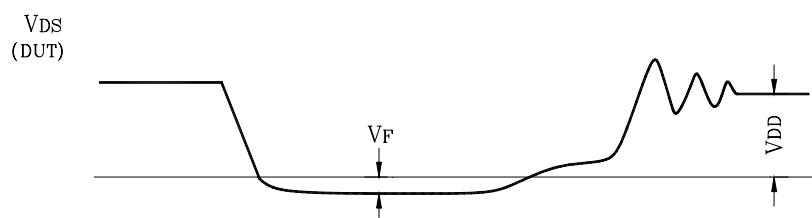
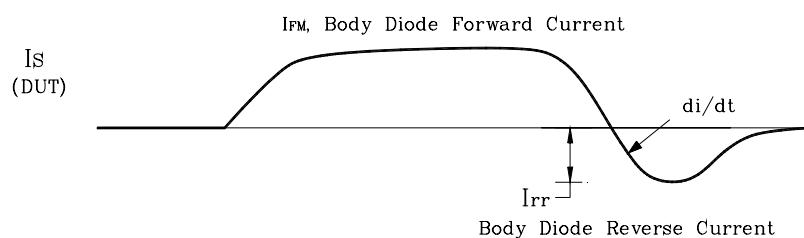
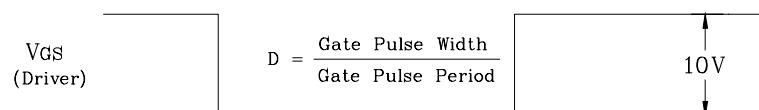
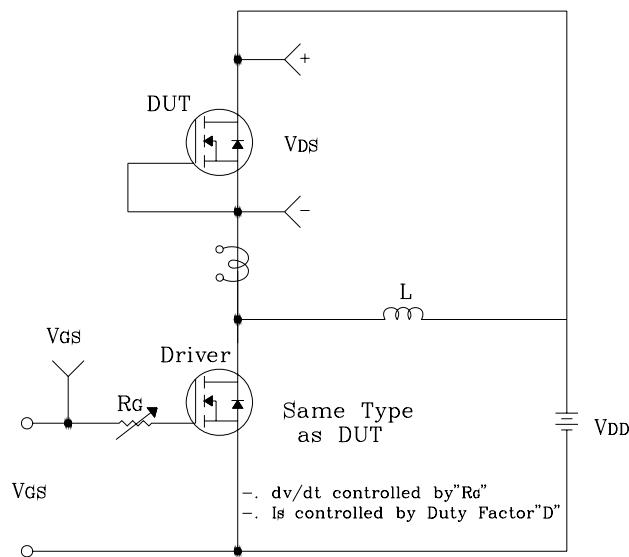
**Fig. 12 Resistive Switching Test Circuit & Waveform**

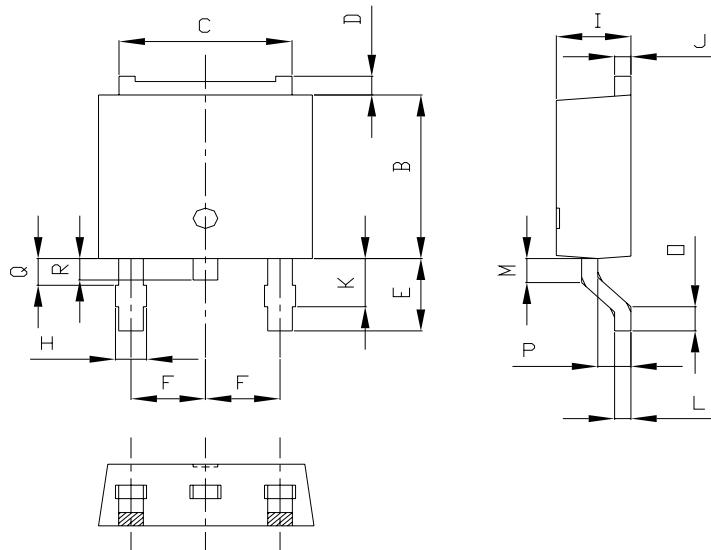


**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

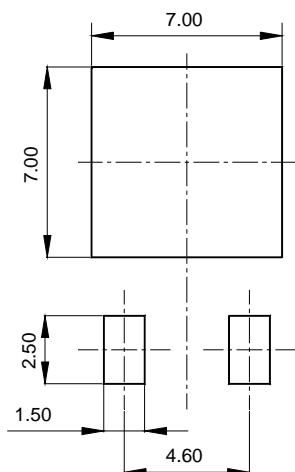


**Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform**



**Outline Dimension**

SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	6.40	6.60	6.80	
B	5.90	6.10	6.30	
C	5.04	5.34	5.64	
D	0.50	0.70	0.90	
E	2.50	2.70	2.90	
F	2.10	2.30	2.50	
H		0.96 MAX		
I	2.20	2.30	2.40	
J	0.40	0.50	0.60	
K	1.60	1.80	2.00	
L	0.40	0.50	0.60	
M	0.81	0.91	1.01	
O	0.80	0.90	1.00	
P	0.90	1.00	1.10	
Q		0.95 MAX		
R	0.60	0.80	1.00	

**※ Recommended Land Pattern [unit: mm]**

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